# Fast recovery Diode RF103L2S

## Applications

High frequency rectification

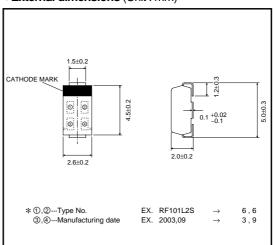
### Features

- 1) Small power mold type (PMDS)
- 2) Ultra low VF
- 3) Very fast recovery
- 4) Low switching loss

### Construction

Silicon epitaxial planar

# ●External dimensions (Unit : mm)



# ● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	VRM	200	V
Reverse voltage (DC)	VR	200	V
Average rectified forward current *	lo	1.0	Α
Forward Peak surge current (60Hz·1cyc.)	IFSM	20	Α
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-40 to +150	°C

<sup>\*</sup> Mounting on glass epoxi board

# ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Тур.	Max.	Unit	Conditions
Forward voltage	VF	0.860	0.920	V	I <sub>F</sub> =1.0A
Reverse current	l <sub>R</sub>	1.2	10	μΑ	V <sub>R</sub> =200V
Reverse recovery time	trr	9	20	nS	I==0.5A
					I <sub>R</sub> =1.0A
					Irr=0.25×IR

## ●Electrical characteristic curves (Ta=25°C)

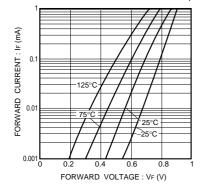


Fig.1 Forward temperature characteristics

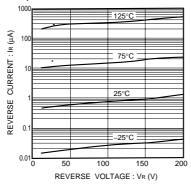


Fig.2 Reverse temperature characteristics

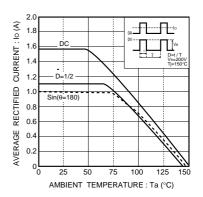


Fig.3 Derating curve

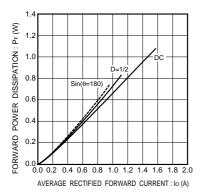


Fig. 4 Power dissipation characteristics

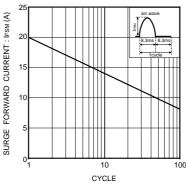


Fig.5 Powerd peak surge current

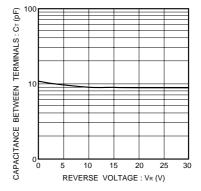


Fig. 6 Capacirance between terminals characteristics

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